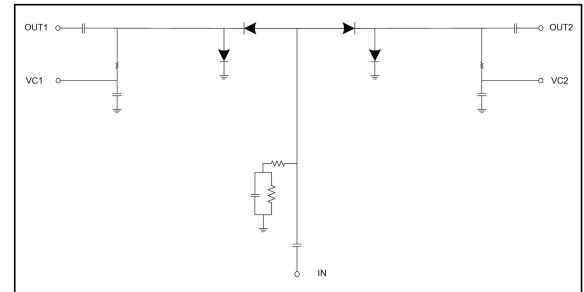


GaAs PIN Reflective SPDT Switch Chip, 2-26GHz

Performance characteristics

- Frequency range: 2-26GHz
- Insertion loss : 0.9dB typ.
- Isolation: 41 dB typ.
- P-1dB: See list
- 50Ohm input / output
- 100% on-wafer testing
- Chip size: 1.77 x 1.32 x 0.1mm
- Silicon nitride passivation, scratch protection

Functional block diagram



Product Introduction

GSW210H is a GaAs PIN reflective single-pole double-throw switch chip with 50Ω matching at the input/output end, a frequency range of 2 to 26 GHz , and -5V/+5V control. It has a built-in bias network and DC blocking capacitors , which is easy to use. It has excellent switching characteristics and port standing wave characteristics in the entire operating frequency range, and is very suitable for microwave hybrid integrated circuits, multi-chip modules, and low-power systems. The switch chip uses on-chip through-hole metallization technology to ensure good grounding, does not require additional grounding measures, and is simple and convenient to use. The back of the chip is metallized, which is suitable for eutectic sintering or conductive adhesive bonding processes.

Use restriction parameter ¹

Maximum input voltage	+2.5V
Maximum input power	+37dBm CW
Operating temperature	-55 ~ +85°C
storage temperature	-65 ~ +150°C

【1】 Exceeding any of these maximum limits may cause permanent damage.

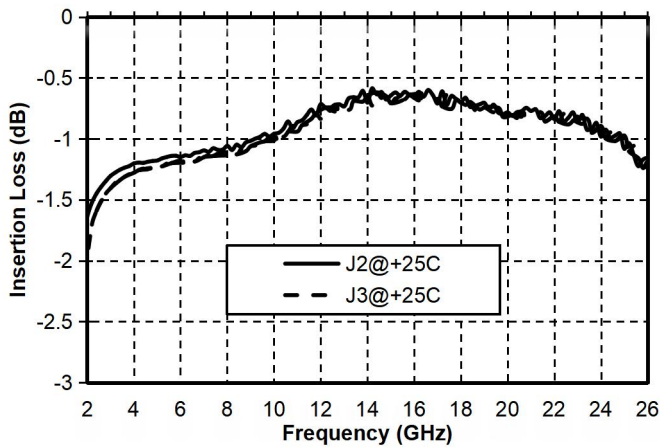
Electrical performance parameters (TA ≈ +25°C)

index	Minimum	Typical Value	Maximum	unit
Frequency Range	2-26			GHz
Insertion loss	-	0.9	-	dB
Isolation	-	41	-	dB
Input return loss	-	19	-	dB
Output return loss	-	20	-	dB
P-1dB	-	25 @ 2 GHz	-	dBm
	-	27 @ 14 GHz	-	dBm
	-	28 @ 18 GHz	-	dBm
	-	26 @ 26 GHz	-	dBm
Switching speed	-	20	-	ns

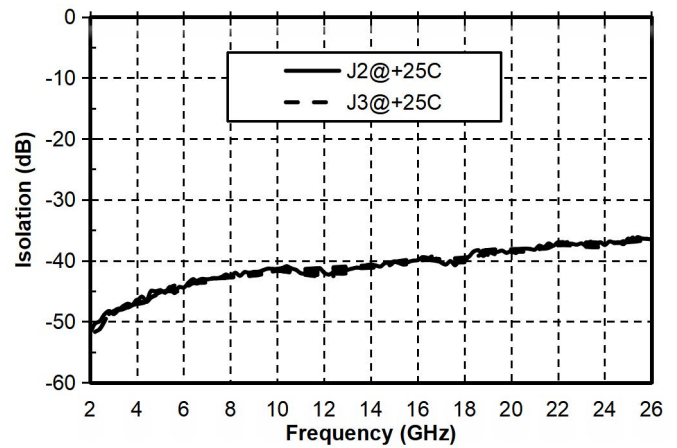
GaAs PIN Reflective SPDT Switch Chip, 2-26GHz

Main index test curve

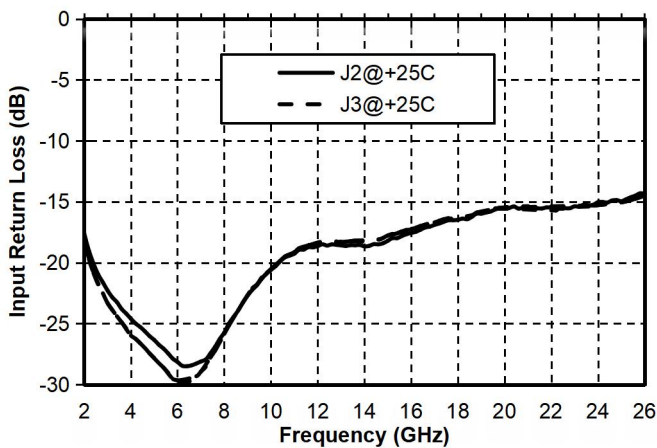
Insertion Loss vs. Operating Frequency



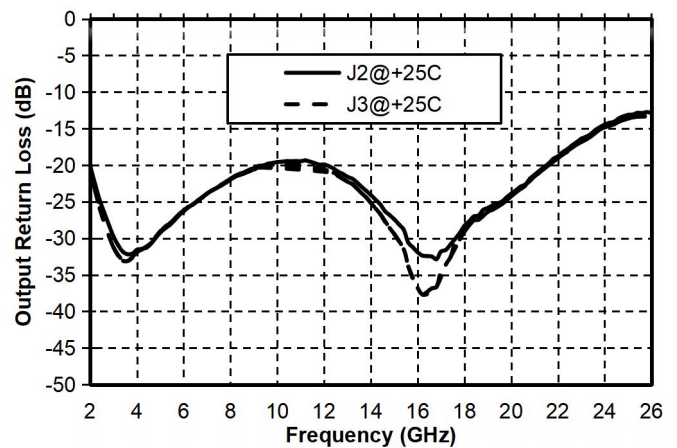
Isolation vs. Operating Frequency



Input Return Loss vs. Frequency



Output Return Loss vs. Frequency



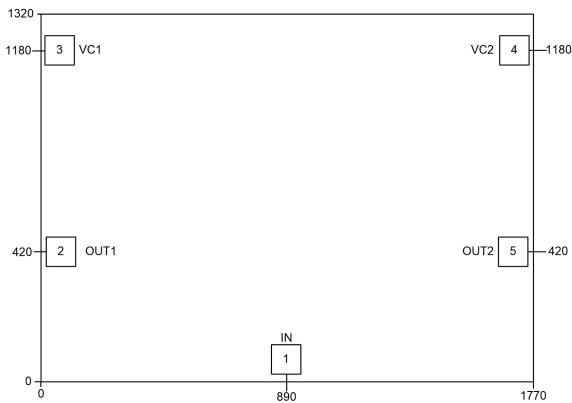
Typical Driver Connections

CONTROL LEVEL (DC CURRENT)		RF OUTPUT STATE	
VC1	VC2	OUT1(J2)-IN(J1)	OUT2(J3)-IN(J1)
-10mA	+15mA	Low Loss	Isolation
+15mA	-10mA	Isolation	Low Loss

Note: $V \approx +2.6\text{ V}$, $I \approx +15\text{ mA}$; $V \approx -3.2\text{ V}$, $I \approx -10\text{ mA}$ (including J1 on-chip resistor $R_{IN} \approx 50$ ohm voltage divider)

GaAs PIN Reflective SPDT Switch Chip, 2-26GHz

Appearance structure

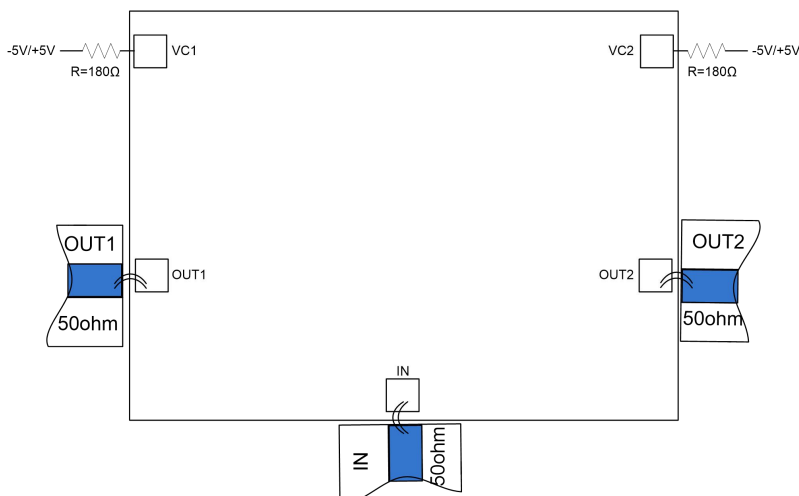


All units in the figure are micrometers

Bonding point definition

Bonding point number	Function Symbol	Functional Description
1	IN(J1)	RF input signal terminal
2, 5	OUT2(J2), OUT3(J3)	RF output signal terminal
3,4	VC1, VC2	Control Port
Chip bottom	GND	The bottom of the chip needs to be well grounded to RF and DC

Recommended circuit diagram



+5V is connected in series with $R \approx 180$ ohm resistor , $V \approx +2.6$ V , $I \approx +15$ mA . -5V is connected in series with $R \approx 180$ ohm resistor , $V \approx -3.2$ V , $I \approx -10$ mA.